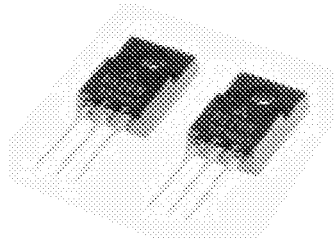


FS2KM-12

HIGH-SPEED SWITCHING USE

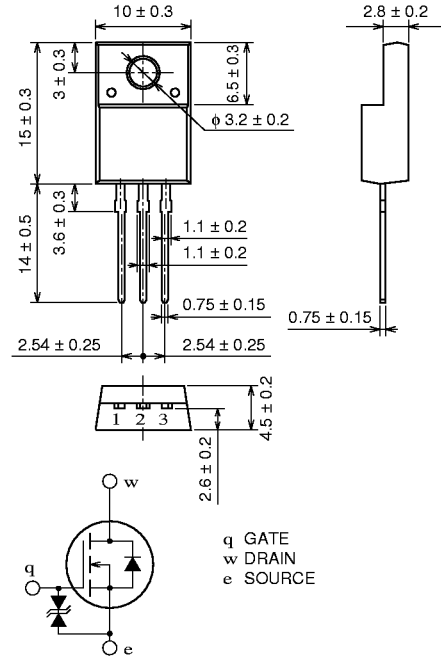
FS2KM-12



• V _{DSS}	600V
• r _{DS} (ON) (MAX)	6.4Ω
• I _D	2A
• V _{iso}	2000V

OUTLINE DRAWING

Dimensions in mm



TO-220FN

APPLICATION

SMPS, DC-DC Converter, battery charger, power supply of printer, copier, HDD, FDD, TV, VCR, personal computer etc.

MAXIMUM RATINGS (T_c = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
V _{DSS}	Drain-source voltage	V _{GS} = 0V	600	V
V _{GSS}	Gate-source voltage	V _{DS} = 0V	±30	V
I _D	Drain current		2	A
I _{DM}	Drain current (Pulsed)		6	A
P _D	Maximum power dissipation		30	W
T _{ch}	Channel temperature		-55 ~ +150	°C
T _{stg}	Storage temperature		-55 ~ +150	°C
V _{iso}	Isolation voltage	AC for 1minute, Terminal to case	2000	V _{rms}
—	Weight	Typical value	2.0	g

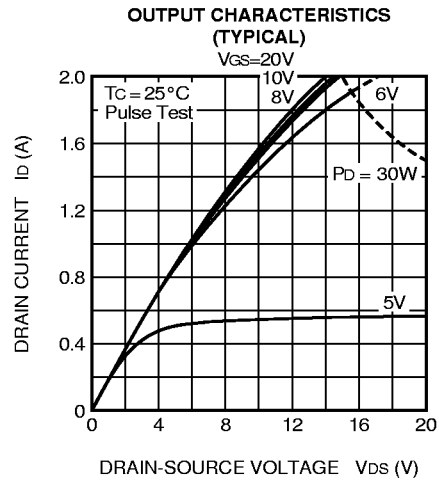
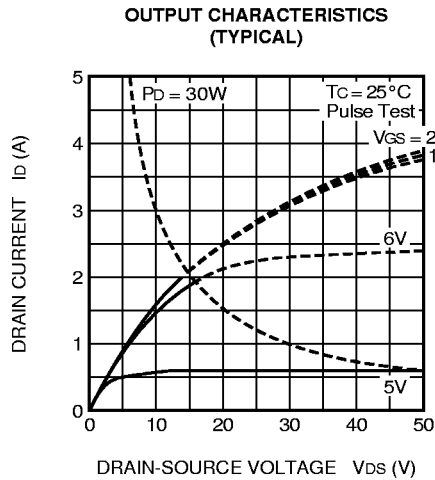
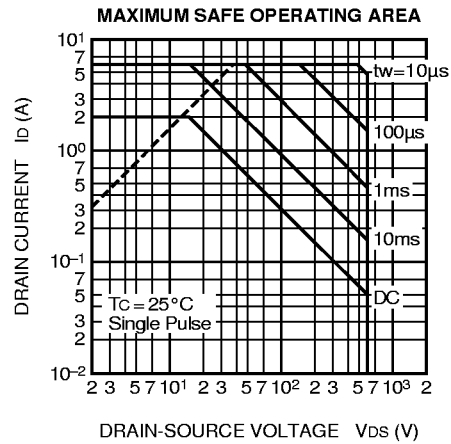
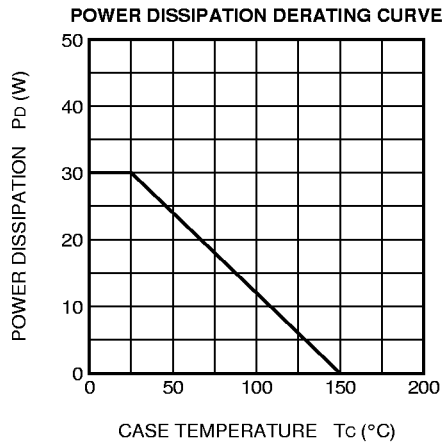
FS2KM-12

HIGH-SPEED SWITCHING USE

ELECTRICAL CHARACTERISTICS (T_{ch} = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V _{(BR) DSS}	Drain-source breakdown voltage	I _D = 1 mA, V _{GS} = 0 V	600	—	—	V
V _{(BR) GSS}	Gate-source breakdown voltage	I _G = ±100 μA, V _{DS} = 0 V	±30	—	—	V
I _{GSS}	Gate-source leakage current	V _{GS} = ±25 V, V _{DS} = 0 V	—	—	±10	μA
I _{DSS}	Drain-source leakage current	V _{DS} = 600 V, V _{GS} = 0 V	—	—	1	mA
V _{GS(th)}	Gate-source threshold voltage	I _D = 1 mA, V _{DS} = 10 V	2	3	4	V
r _{DS(on)}	Drain-source on-state resistance	I _D = 1 A, V _{GS} = 10 V	—	5.0	6.4	Ω
V _{DS(on)}	Drain-source on-state voltage	I _D = 1 A, V _{GS} = 10 V	—	5.0	6.4	V
y _{fs}	Forward transfer admittance	I _D = 1 A, V _{DS} = 10 V	0.8	1.3	—	S
C _{iss}	Input capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz	—	300	—	pF
C _{oss}	Output capacitance		—	30	—	pF
C _{rss}	Reverse transfer capacitance		—	5	—	pF
t _{d(on)}	Turn-on delay time	V _{DD} = 200 V, I _D = 1 A, V _{GS} = 10 V, R _{GEN} = R _{GS} = 50 Ω	—	13	—	ns
t _r	Rise time		—	10	—	ns
t _{d(off)}	Turn-off delay time		—	30	—	ns
t _f	Fall time		—	30	—	ns
V _{SD}	Source-drain voltage	I _S = 1 A, V _{GS} = 0 V	—	1.5	2.0	V
R _{th(ch-c)}	Thermal resistance	Channel to case	—	—	4.17	°C/W

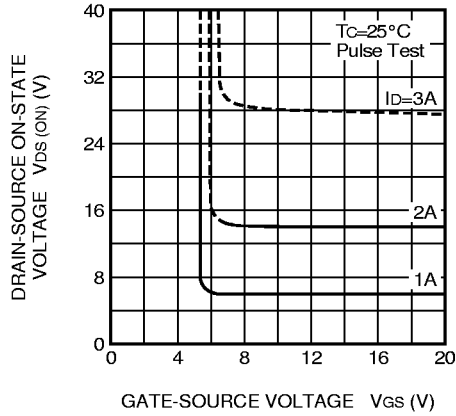
PERFORMANCE CURVES



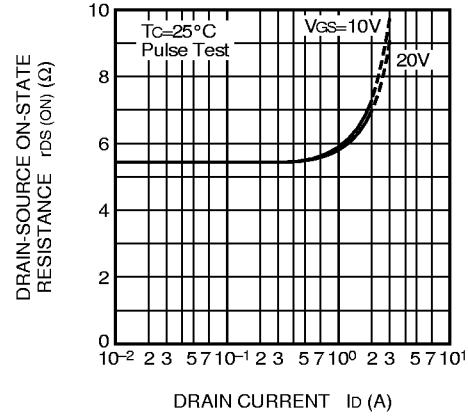
FS2KM-12

HIGH-SPEED SWITCHING USE

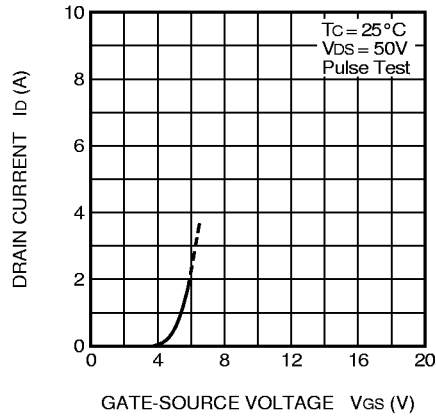
ON-STATE VOLTAGE VS.
GATE-SOURCE VOLTAGE
(TYPICAL)



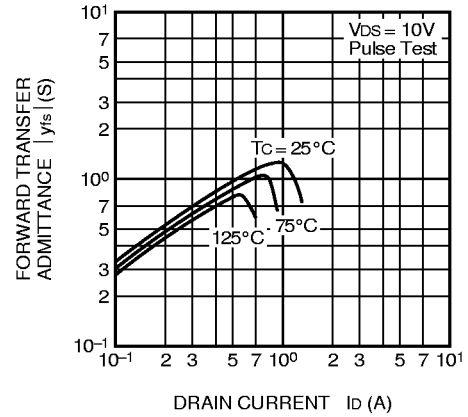
ON-STATE RESISTANCE VS.
DRAIN CURRENT
(TYPICAL)



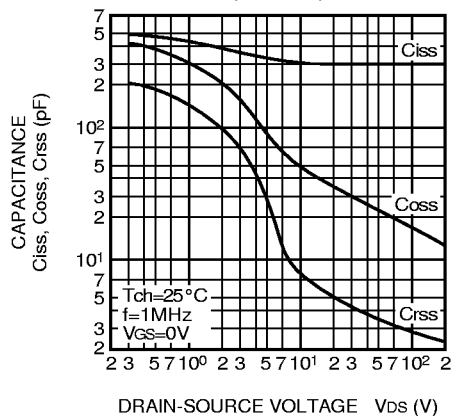
TRANSFER CHARACTERISTICS
(TYPICAL)



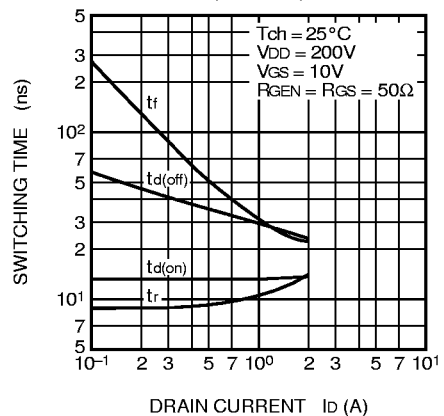
FORWARD TRANSFER ADMITTANCE
VS. DRAIN CURRENT
(TYPICAL)



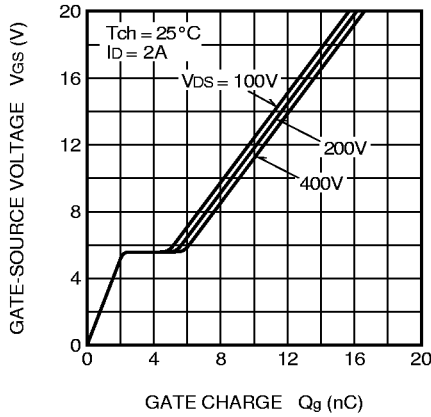
CAPACITANCE VS.
DRAIN-SOURCE VOLTAGE
(TYPICAL)



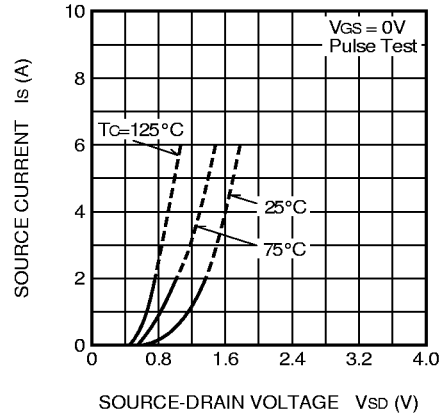
SWITCHING CHARACTERISTICS
(TYPICAL)



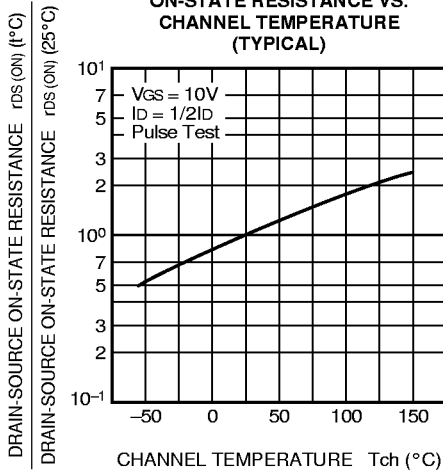
GATE-SOURCE VOLTAGE
VS. GATE CHARGE
(TYPICAL)



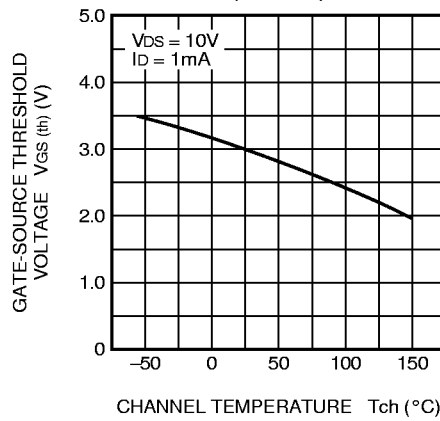
SOURCE-DRAIN DIODE
FORWARD CHARACTERISTICS
(TYPICAL)



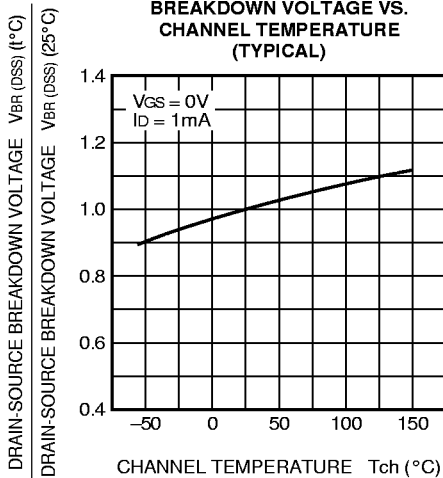
ON-STATE RESISTANCE VS.
CHANNEL TEMPERATURE
(TYPICAL)



THRESHOLD VOLTAGE VS.
CHANNEL TEMPERATURE
(TYPICAL)



BREAKDOWN VOLTAGE VS.
CHANNEL TEMPERATURE
(TYPICAL)



TRANSIENT THERMAL IMPEDANCE
CHARACTERISTICS

